

LISTING OF CLAIMS:

1. (Currently amended) A semiconductor pressure sensor device comprising:

a conductive member;

a sensor chip for detecting a pressure and generating an electrical signal corresponding to the pressure;

a bonding pad that is formed of an aluminum base material and provided on a surface of the sensor chip;

a bonding wire electrically connecting the ~~sensor chip~~bonding pad and the conductive member; and

a protective member having characteristics of electric insulation and plasticity and covering the sensor chip and the bonding wire,

wherein the bonding wire is formed of an alloy of Au and Pd, and the protective member is formed of a fluorine gel.

2. (Original) The pressure sensor device of Claim 1,

wherein a diameter of the bonding wire is not larger than 40 μm .

3. (Original) The pressure sensor device of Claim 1, further comprising:

a circuit chip for processing the electrical signal from the sensor chip; and

an additional bonding wire electrically connecting the circuit chip and the sensor chip,

wherein the protective member covers the circuit sensor chip and the bonding wire, and

wherein the additional bonding wire is formed of an alloy of Au and Pd.

4. (Original) The pressure sensor device of Claim 3,

wherein a diameter of the additional bonding wire is not larger than 40 μm